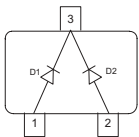


**Silicon Low Leakage Diode Array**

- Low-leakage applications
- Medium speed switching times
- Pb-free (RoHS compliant) package <sup>1)</sup>
- Qualified according AEC Q101


**BAV170**


| Type   | Package | Configuration  | Marking |
|--------|---------|----------------|---------|
| BAV170 | SOT23   | common cathode | JXs     |

**Maximum Ratings** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter  | Symbol    | Value       | Unit             |
|--|-----------|-------------|------------------|
| Diode reverse voltage                                  | $V_R$     | 80          | V                |
| Peak reverse voltage                                   | $V_{RM}$  | 85          |                  |
| Forward current  | $I_F$     | 200         | mA               |
| Non-repetitive peak surge forward current              | $I_{FSM}$ |             | A                |
| $t = 1 \mu\text{s}$                                    |           | 4.5         |                  |
| $t = 1 \text{s}$                                       |           | 0.5         |                  |
| Total power dissipation<br>$T_S \leq 35^\circ\text{C}$ | $P_{tot}$ | 250         | mW               |
| Junction temperature                                   | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature                                    | $T_{stg}$ | -65 ... 150 |                  |

**Thermal Resistance**

| Parameter  | Symbol     | Value      | Unit |
|--|------------|------------|------|
| Junction - soldering point <sup>2)</sup><br>BAV170 | $R_{thJS}$ | $\leq 460$ | K/W  |

<sup>1)</sup>Pb-containing package may be available upon special request

<sup>2)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter   | Symbol     | Values |      |                             | Unit |
|---|------------|--------|------|-----------------------------|------|
|   |            | min.   | typ. | max.                        |      |
| <b>DC Characteristics</b>   |            |        |      |                             |      |
| Breakdown voltage<br>$I_{(BR)} = 100 \mu\text{A}$   | $V_{(BR)}$ | 85     | -    | -                           | V    |
| Reverse current<br>$V_R = 75 \text{ V}$<br>$V_R = 75 \text{ V}, T_A = 150^\circ\text{C}$                            | $I_R$      | -      | -    | 5<br>80                     | nA   |
| Forward voltage<br>$I_F = 1 \text{ mA}$<br>$I_F = 10 \text{ mA}$<br>$I_F = 50 \text{ mA}$<br>$I_F = 150 \text{ mA}$ | $V_F$      | -      | -    | 900<br>1000<br>1100<br>1250 | mV   |

**AC Characteristics**

|  |          |   |     |     |               |
|--|----------|---|-----|-----|---------------|
| Diode capacitance<br>$V_R = 0 \text{ V}, f = 1 \text{ MHz}$  | $C_T$    | - | 2   | -   | pF            |
| Reverse recovery time<br>$I_F = 10 \text{ mA}, I_R = 10 \text{ mA}$ , measured at $I_R = 1 \text{ mA}$ ,<br>$R_L = 100 \Omega$ | $t_{rr}$ | - | 0.6 | 1.5 | $\mu\text{s}$ |

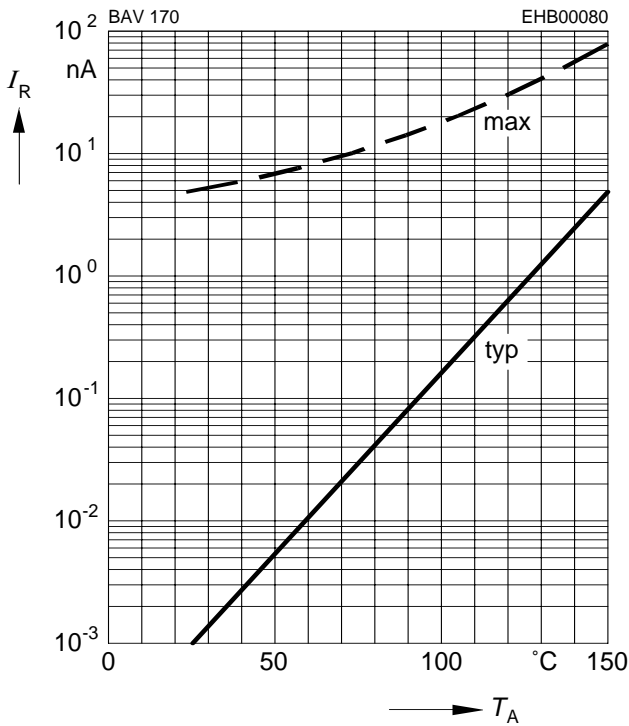
**Test circuit for reverse recovery time**


Pulse generator:  $t_p = 10 \mu\text{s}$ ,  $D = 0.05$ ,  $t_r = 0.6 \text{ ns}$ ,  
 $R_i = 50 \Omega$

Oscilloscope:  $R = 50 \Omega$ ,  $t_r = 0.35 \text{ ns}$ ,  $C \leq 1 \text{ pF}$

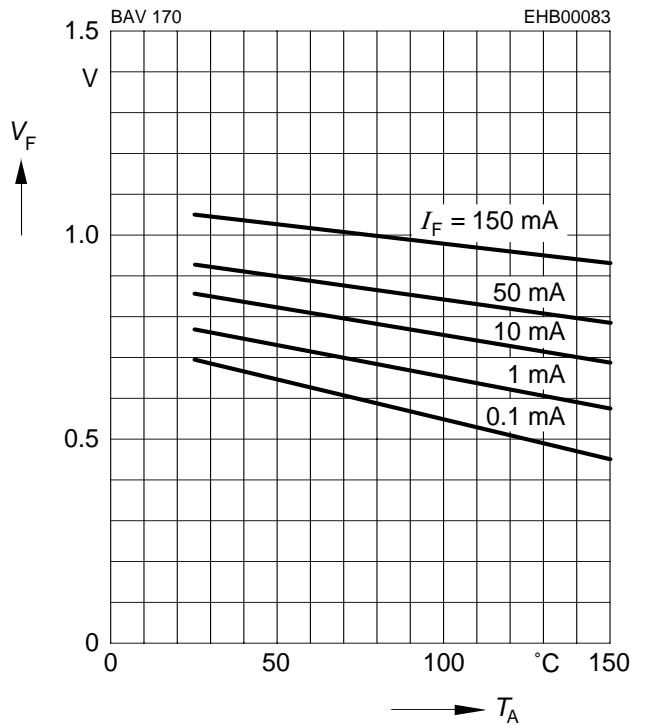
**Reverse current  $I_R = f(T_A)$**

$V_R = 70V$



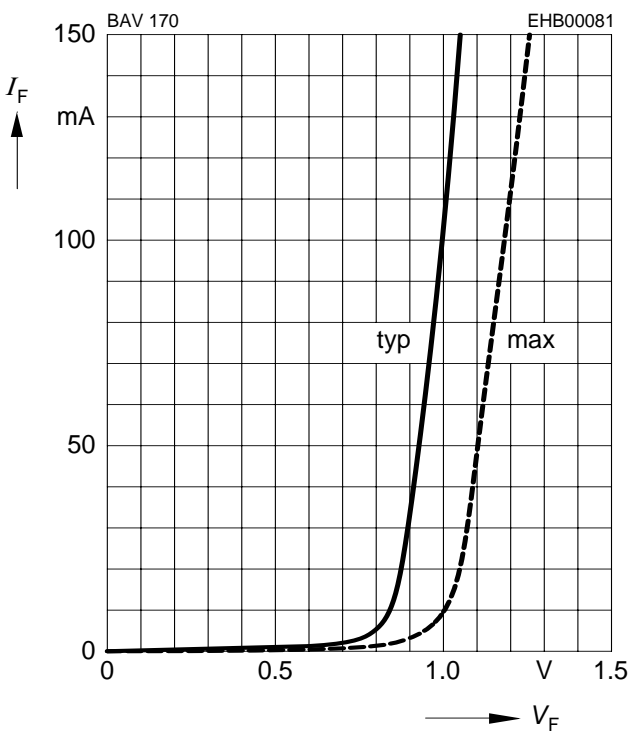
**Forward Voltage  $V_F = f(T_A)$**

$I_F = \text{Parameter}$



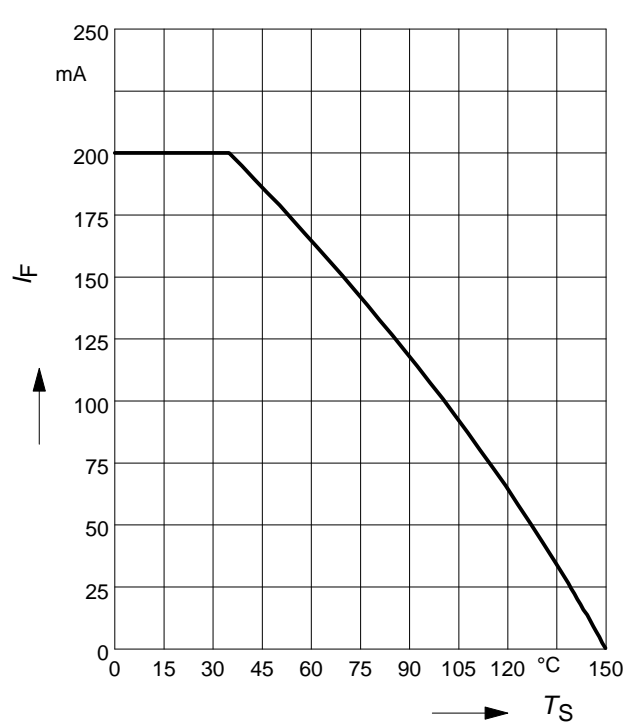
**Forward current  $I_F = f(V_F)$**

$T_A = 25^\circ\text{C}$

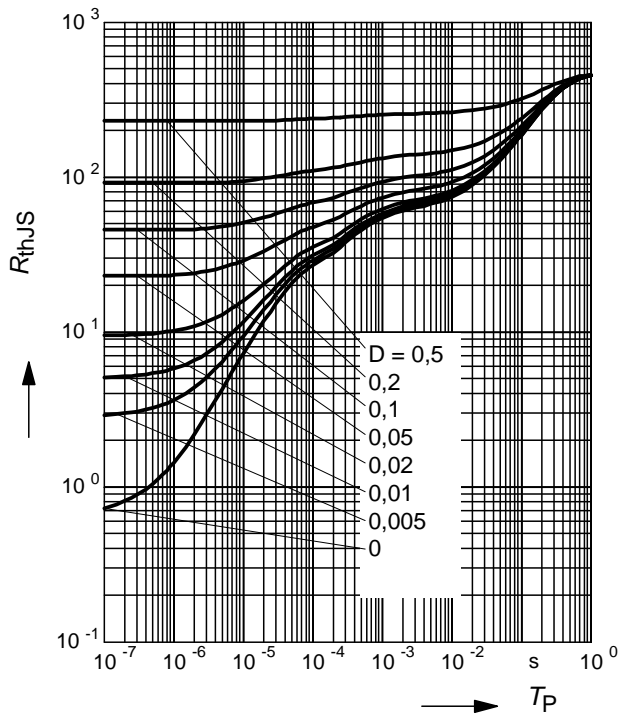


**Forward current  $I_F = f(T_S)$**

BAV170

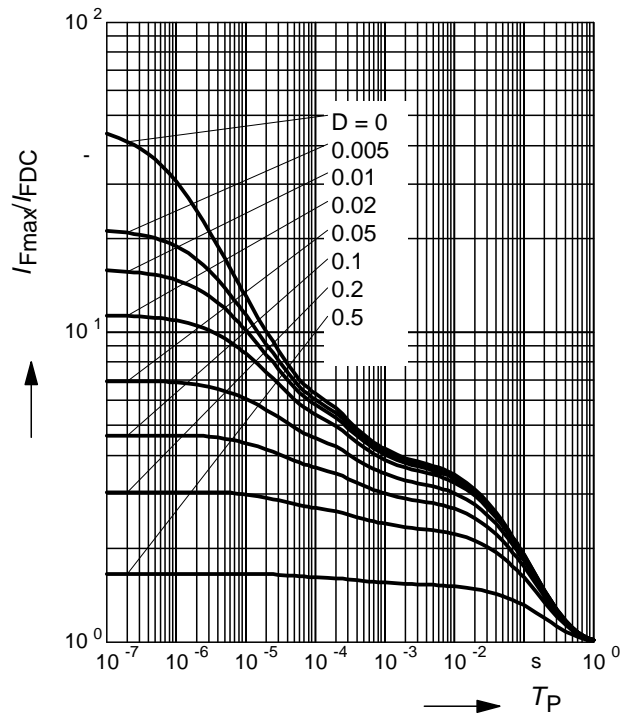


Permissible Puls Load  $R_{thJS} = f(t_p)$



Permissible Pulse Load

$I_{Fmax} / I_{FDC} = f(t_p)$



Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



Edition 2006-02-01  
Published by  
Infineon Technologies AG  
81726 München, Germany  
© Infineon Technologies AG 2007.  
All Rights Reserved.

### **Attention please!**

The information given in this dokument shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

### **Information**

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

### **Warnings**

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9